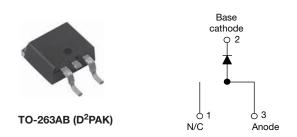
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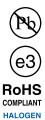
High Performance Schottky Rectifier, 8 A



PRODUCT SUMMARY							
Package	TO-263AB (D ² PAK)						
I _{F(AV)}	8 A						
V _R	80 V, 100 V						
V _F at I _F	0.72 V						
I _{RM} max.	7 mA at 125 °C						
T _J max.	175 °C						
Diode variation	Single die						
E _{AS}	7.5 mJ						

FEATURES

- 175 °C T_J operation
- Low forward voltage drop
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance



FREE

- Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

The VS-8TQ... Schottky rectifier series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	CHARACTERISTICS VALUES UN						
I _{F(AV)}	Rectangular waveform	8	А					
V _{RRM}	Range	80, 100	V					
I _{FSM}	t _p = 5 μs sine	850	А					
V _F	8 A _{pk} , T _J = 125 °C	0.58	V					
TJ	Range	-55 to +175	°C					

VOLTAGE RATINGS								
PARAMETER	SYMBOL	VS-8TQ080SPbF	VS-8TQ100SPbF	UNITS				
Maximum DC reverse voltage	V _R	80	100	V				
Maximum working peak reverse voltage	V _{RWM}	00	100					

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST COND	VALUES	UNITS					
Maximum average forward current See fig. 5	I _{F(AV)}	50 % duty cycle at $T_C = 157 \text{ °C}$	8	А					
Maximum peak one cycle non-repetitive surge current	I _{FSM}	5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated	850	A				
See fig. 7		10 ms sine or 6 ms rect. pulse	V _{RRM} applied	230					
Non-repetitive avalanche energy	E _{AS}	$T_J = 25 \ ^{\circ}C, \ I_{AS} = 0.50 \ A, \ L = 60$	7.50	mJ					
Repetitive avalanche current	I _{AR}	Current decaying linearly to zer Frequency limited by T _J maxim	0.50	А					

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ELECTRICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS					
		8 A	T _{.1} = 25 °C	0.72				
Maximum forward voltage drop	V (1)	16 A	1j=25 C	0.88	V			
See fig. 1	V _{FM} ⁽¹⁾	8 A	T 105 %O	0.58				
		16 A	T _J = 125 °C	0.69				
Maximum reverse leakage current	I _{RM} (1)	T _J = 25 °C	V = Poted V	0.55				
See fig. 2		T _J = 125 °C	$V_R = Rated V_R$	7	mA			
Maximum junction capacitance	aximum junction capacitance C_T $V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz), 25 °C		500	pF				
Typical series inductance	L _S	Measured lead to lead 5 n	8	nH				
Maximum voltage rate of change	dV/dt	Rated V _R	10 000	V/µs				

Note

 $^{(1)}\,$ Pulse width < 300 $\mu s,$ duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range		T _J , T _{Stg}		-55 to +175	°C			
Maximum thermal resistance, junction to case		R _{thJC}	DC operation See fig. 4	2.0	°C/W			
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.50	0/11			
Approximate weight				2	g			
Approximate weight				0.07	oz.			
Mounting torque	minimum			6 (5)	kgf ⋅ cm			
Mounting torque	maximum			12 (10)	(lbf ⋅ in)			
			$\rho_{\rm res}$ at $h = D^2 D A K$	8TQ080S				
Marking device			Case style D ² PAK	8TQ100S				



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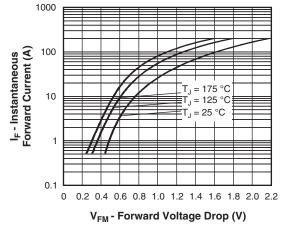


Fig. 1 - Maximum Forward Voltage Drop Characteristics

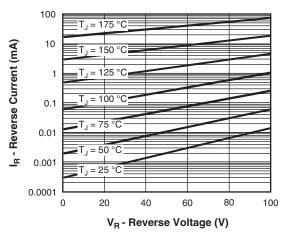


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

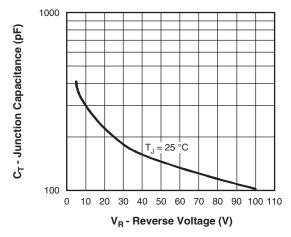
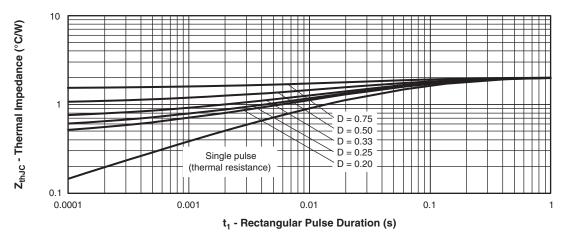
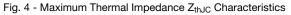


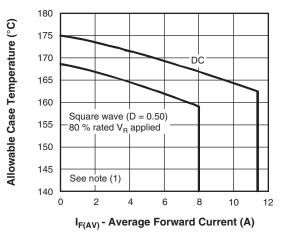
Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



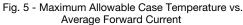


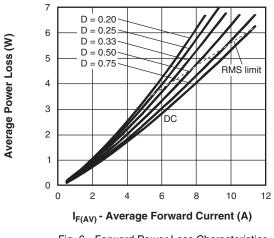
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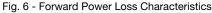
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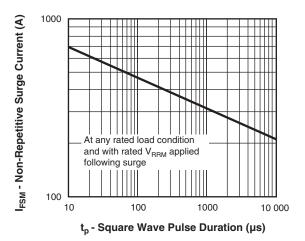


Fig. 7 - Maximum Non-Repetitive Surge Current

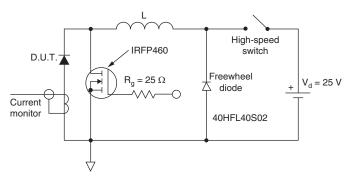


Fig. 8 - Unclamped Inductive Test Circuit

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see fig. 6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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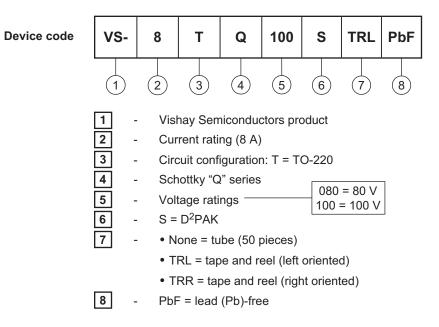
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SPICE models	www.vishay.com/doc?95291					

Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

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SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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